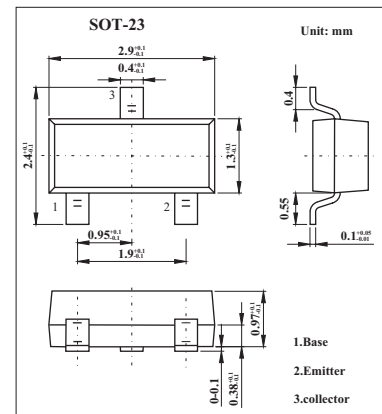


## Silicon NPN Epitaxial

## 2SC2463

## ■ Features

- Low frequency amplifier.

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CB0}$	55	V
Collector-emitter voltage	$V_{CE0}$	50	V
Emitter-base voltage	$V_{EB0}$	5	V
Collector current	$I_C$	100	mA
Collector dissipation	$P_C$	150	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 10\mu\text{A}$ , $I_E = 0$	55			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1\text{mA}$ , $R_{BE} = \infty$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 10\mu\text{A}$ , $I_C = 0$	5			V
Collector cutoff current	$I_{CBO}$	$V_{CB} = 30\text{V}$ , $I_E = 0$			0.5	$\mu\text{A}$
Emitter cutoff current	$I_{EBO}$	$V_{EB} = 2\text{V}$ , $I_C = 0$			0.5	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE} = 12\text{V}$ , $I_C = 2\text{mA}$	250		1200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10\text{mA}$ , $I_B = 1\text{mA}$			0.5	V
Base-emitter voltage	$V_{BE}$	$V_{CE} = 12\text{V}$ , $I_C = 2\text{mA}$			0.75	V

■  $h_{FE}$  Classification

Marking	DD	DE	DF
$h_{FE}$	250~500	400~800	600~1200